METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A technique includes: forming a film containing first and second elements on a substrate by performing: forming a first layer containing the first element by performing, a first number of times, a cycle including: (a-1) supplying a first precursor gas containing the first element to the substrate; and (a-2) supplying a first reaction gas to the substrate; and forming a second layer containing the first and second elements by performing, a second number of times, a cycle including: (b-1) supplying a second precursor gas containing the first element and a first halogen element to the substrate; (b-2) supplying a third precursor gas, which contains the second element and a second halogen element, to the substrate, after supplying the second precursor gas for a first period in (b-1); and (b-3) supplying a second reaction gas to the substrate, after supplying the third precursor gas for a second period in (b-2).

Fig. 4